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APR 18 2006

S/N

10/804,610

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

KITAOKA, et al.

Examiner:

T. Ho

Serial No.:

10/804,610

Group Art Unit:

2818

Filed:

March 18, 2004

Docket:

10873.1420US01

Title:

METHOD OF MANUFACTURING GROUP III NITRIDE

SUBSTRATE AND SEMICONDUCTOR DEVICE

CERTIFICATE UNDER 37 CFR 1.6(d): I hereby certify that this paper is being transmitted by facsimile to the U.S. Patent and Trademark Office on April 18, 2006.

Name: Peggy Kerkhovc

INFORMATION DISCLOSURE STATEMENT (37 C.F.R. § 1.97(c))

Mail Stop RCE Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner. Applicants hereby bring attention to the Examiner that they have three commonly assigned co-pending applications, Serial No. 10/758,815 (US Publication No. 2004-0147096) filed January 16, 2004, Serial No. 10/884,252 (US Publication No. 2005-0011432) filed July 2, 2004 and Serial No. 10/969,791 (US Publication No. 2005-0082564) filed October 19, 2004.

This statement should be considered because it is submitted before the mailing date of a first Office Action on-the-merits after filing a Request for Continued Examination under 37 C.F.R. § 1.114. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

In accordance with 37 C.F.R. §1.98(a)(2), a copy of each foreign document or other information listed on the enclosed Form 1449 is provided. As this application was filed after June 30, 2003, copies of the cited U.S. Patent Documents are not included.

Noted 1 7H 06/2006 Date Mailed: April 18, 2006

Shoot 1 of 1

FORM 1449*	INFORMATION DISCLOSURE STATEMENT	Docket Number: 10873.1420US01	Application Number: 10/804,610
	IN AN APPLICATION	Applicant: KITAOKA, ct al.	
	(Use several shoots if necessary)	Filing Date; March 18, 2004	Group Art Unit; 2818

		U.S.	PATENT DOCUMEN	its .			
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS		G DATE OPRIATE
TH	6,121,121	September, 2000	Koide	438	481		
	6,503,610	January, 2003	Hiramatsu, et al.	428	210		· · · · · · · · · · · · · · · · · · ·
	6.667,252	Documber, 2003	Miyajima, et al.	438	796		,
<u> </u>	2005/0082564	April, 2005	Kitaoka, et al.	257	103		
							
	DOCUMENT NO.	FOREIG	N PATENT DOCUM	ENT\$	SUBCLASS		
	2002	JANE 1	COOMIKI	CLASS	SUBCLASS	YES	LATION
TH	3409576	March, 2003	Japan			Abstract	110
TH	2000-357663	December, 20003	Japan			Abstract	
	ОТНЕІ	R DOCUMENTS (In	cluding Author, Title, I	Date, Pertinent P	ages, Etc.)		
TH	Kawamura, et al., "Growth of a Large GaN Single Crystal Using the Liquid Phase Epitaxy (LPE)Technique", Jpn. J. Appl. Phys., vol. 42, part 2, no. 1A/B, January 15, 2003, pp. L4-L6						
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	EXAMINER	ru Tu Ho/ (06/16/2006)	DATE CONSIDERED	06/16/2006

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.